

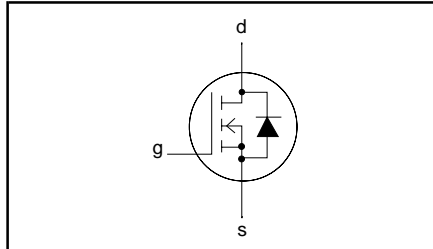
N-channel TrenchMOS™ transistor

PHP30NQ15T, PHB30NQ15T

FEATURES

- 'Trench' technology
- Very low on-state resistance
- Fast switching
- Low thermal resistance

SYMBOL



QUICK REFERENCE DATA

| |
|-------------------------------------|
| $V_{DSS} = 150\text{ V}$ |
| $I_D = 29\text{ A}$ |
| $R_{DS(ON)} \leq 63\text{ m}\Omega$ |

GENERAL DESCRIPTION

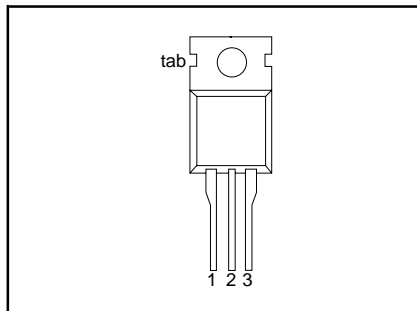
N-channel enhancement mode field-effect power transistor in a plastic envelope using 'trench' technology. The device has very low on-state resistance. It is intended for use in dc to dc converters and general purpose switching applications.

The PHP30NQ15T is supplied in the SOT78 (TO220AB) conventional leaded package.
The PHB30NQ15T is supplied in the SOT404 (D²PAK) surface mounting package.

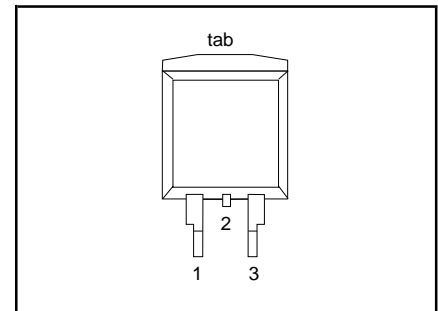
PINNING

| PIN | DESCRIPTION |
|-----|--------------------|
| 1 | gate |
| 2 | drain ¹ |
| 3 | source |
| tab | drain |

SOT78 (TO220AB)



SOT404 (D²PAK)



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134)

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
|----------------|--|--|------|----------|------------------|
| V_{DSS} | Drain-source voltage | $T_j = 25\text{ }^\circ\text{C}$ to $175\text{ }^\circ\text{C}$ | - | 150 | V |
| V_{DGR} | Drain-gate voltage | $T_j = 25\text{ }^\circ\text{C}$ to $175\text{ }^\circ\text{C}$; $R_{GS} = 20\text{ k}\Omega$ | - | 150 | V |
| V_{GS} | Gate-source voltage | | - | ± 20 | V |
| I_D | Continuous drain current | $T_{mb} = 25\text{ }^\circ\text{C}$; $V_{GS} = 10\text{ V}$ | - | 29 | A |
| | | $T_{mb} = 100\text{ }^\circ\text{C}$; $V_{GS} = 10\text{ V}$ | - | 20 | A |
| I_{DM} | Pulsed drain current | $T_{mb} = 25\text{ }^\circ\text{C}$ | - | 116 | A |
| P_D | Total power dissipation | $T_{mb} = 25\text{ }^\circ\text{C}$ | - | 150 | W |
| T_j, T_{stg} | Operating junction and storage temperature | | -55 | 175 | $^\circ\text{C}$ |

¹ It is not possible to make connection to pin:2 of the SOT404 package

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PHP30NQ15T, PHB30NQ15T

AVALANCHE ENERGY LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134)

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
|----------|----------------------------------|--|------|------|------|
| E_{AS} | Non-repetitive avalanche energy | Unclamped inductive load, $I_{AS} = 26$ A; $t_p = 0.2$ ms; T_j prior to avalanche = 25°C ; $V_{DD} \leq 25$ V; $R_{GS} = 50$ Ω ; $V_{GS} = 10$ V; refer to fig:15 | - | 502 | mJ |
| I_{AS} | Non-repetitive avalanche current | | - | 29 | A |

THERMAL RESISTANCES

| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|----------------|--|--|------|------|------|------|
| $R_{th\ j-mb}$ | Thermal resistance junction to mounting base | | - | - | 1 | K/W |
| $R_{th\ j-a}$ | Thermal resistance junction to ambient | SOT78 in free air | - | 60 | - | K/W |
| | | SOT404 package, pcb mounted, minimum footprint | - | 50 | - | K/W |

ELECTRICAL CHARACTERISTICS $T_j = 25^\circ\text{C}$ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|---------------|----------------------------------|--|-------------|--------|-----------|--------------------------|
| $V_{(BR)DSS}$ | Drain-source breakdown voltage | $V_{GS} = 0$ V; $I_D = 0.25$ mA; $T_j = -55^\circ\text{C}$ | 150 133 | - | - | V V |
| $V_{GS(TO)}$ | Gate threshold voltage | $V_{DS} = V_{GS}$; $I_D = 1$ mA $T_j = 175^\circ\text{C}$ $T_j = -55^\circ\text{C}$ | 2 1 - | 3 - | 4 - | V V V |
| $R_{DS(ON)}$ | Drain-source on-state resistance | $V_{GS} = 10$ V; $I_D = 15$ A $T_j = 175^\circ\text{C}$ | - | 60 | 63 176 | m Ω m Ω |
| I_{GSS} | Gate source leakage current | $V_{GS} = \pm 10$ V; $V_{DS} = 0$ V | - | 0.02 | 100 | nA |
| I_{DSS} | Zero gate voltage drain current | $V_{DS} = 150$ V; $V_{GS} = 0$ V; $T_j = 175^\circ\text{C}$ | - | 0.05 | 10 500 | μ A μ A |
| $Q_{g(tot)}$ | Total gate charge | $I_D = 30$ A; $V_{DD} = 120$ V; $V_{GS} = 10$ V | - | 55 | - | nC |
| Q_{gs} | Gate-source charge | | - | 10 | - | nC |
| Q_{gd} | Gate-drain (Miller) charge | | - | 20 | - | nC |
| $t_{d\ on}$ | Turn-on delay time | $V_{DD} = 75$ V; $R_D = 2.7$ Ω ; $V_{GS} = 10$ V; $R_G = 5.6$ Ω Resistive load | - | 14 | - | ns |
| t_r | Turn-on rise time | | - | 50 | - | ns |
| $t_{d\ off}$ | Turn-off delay time | | - | 48 | - | ns |
| t_f | Turn-off fall time | | - | 38 | - | ns |
| L_d | Internal drain inductance | Measured tab to centre of die | - | 3.5 | - | nH |
| L_s | Internal source inductance | Measured from source lead to source bond pad | - | 7.5 | - | nH |
| C_{iss} | Input capacitance | $V_{GS} = 0$ V; $V_{DS} = 25$ V; $f = 1$ MHz | - | 2390 | - | pF |
| C_{oss} | Output capacitance | | - | 240 | - | pF |
| C_{rss} | Feedback capacitance | | - | 98 | - | pF |

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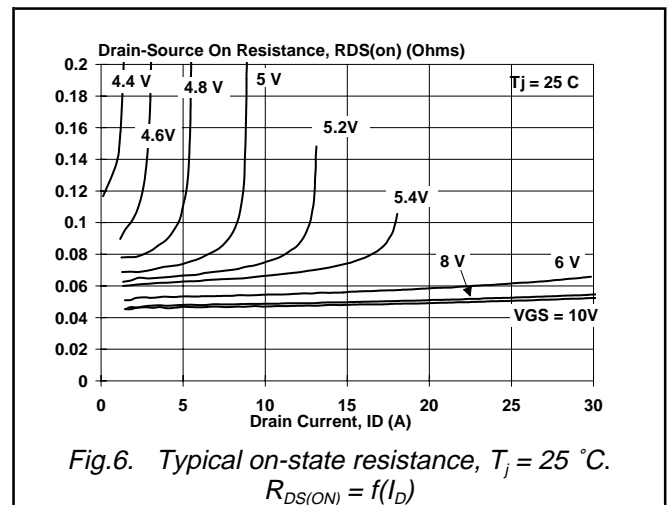
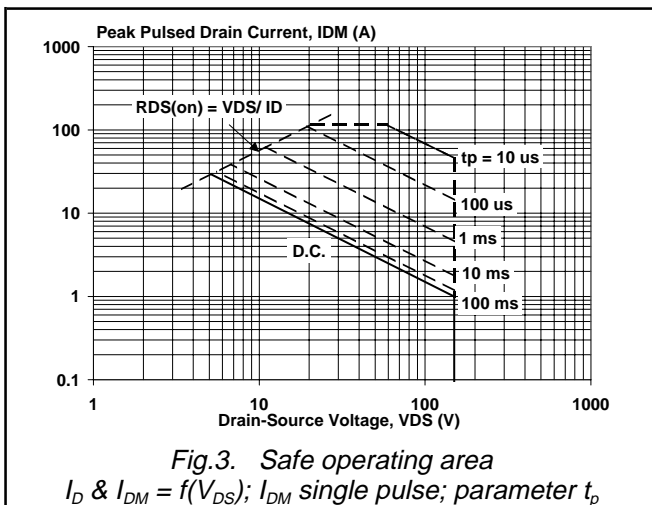
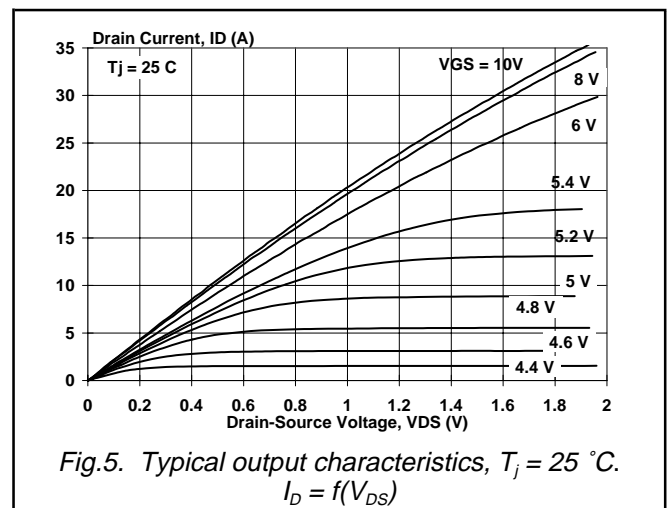
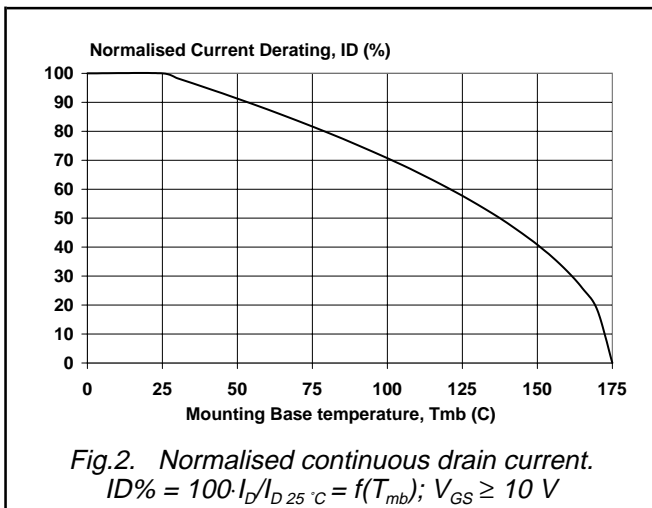
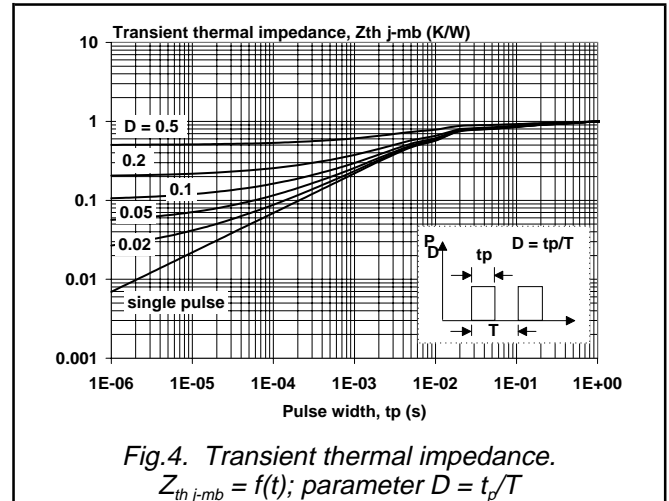
PHP30NQ15T, PHB30NQ15T

REVERSE DIODE LIMITING VALUES AND CHARACTERISTICS $T_j = 25^\circ\text{C}$ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|----------|--|---|------|------|------|---------------|
| I_S | Continuous source current (body diode) | | - | - | 29 | A |
| I_{SM} | Pulsed source current (body diode) | | - | - | 116 | A |
| V_{SD} | Diode forward voltage | $I_F = 25\text{ A}; V_{GS} = 0\text{ V}$ | - | 0.9 | 1.2 | V |
| t_{rr} | Reverse recovery time | $I_F = 20\text{ A}; -di_F/dt = 100\text{ A}/\mu\text{s};$ $V_{GS} = 0\text{ V}; V_R = 25\text{ V}$ | - | 105 | - | ns |
| Q_{rr} | Reverse recovery charge | | - | 0.55 | - | μC |

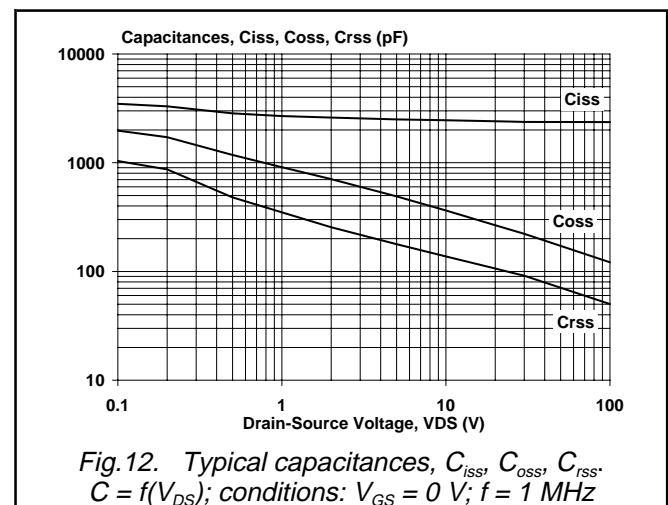
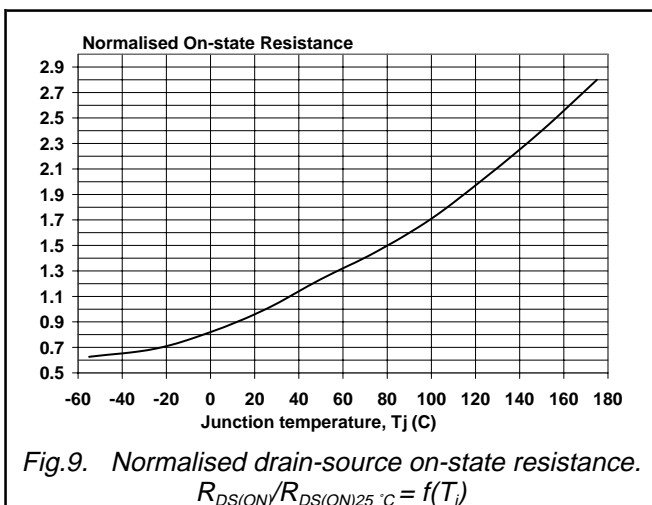
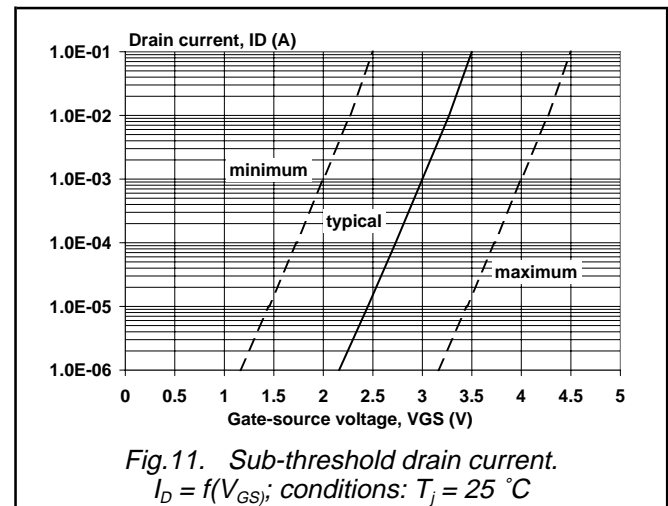
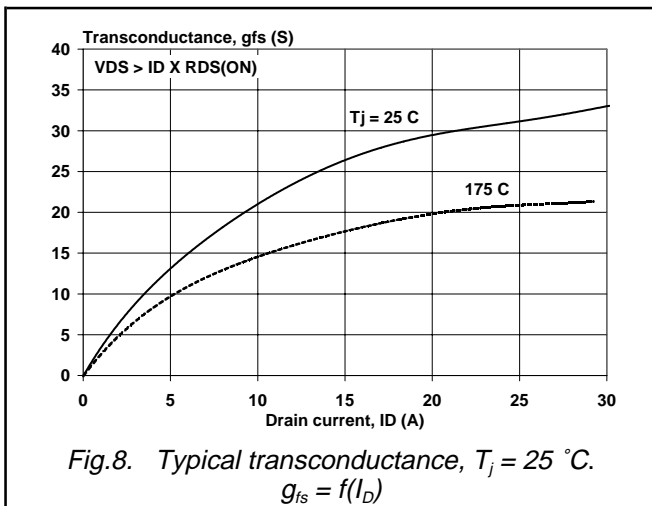
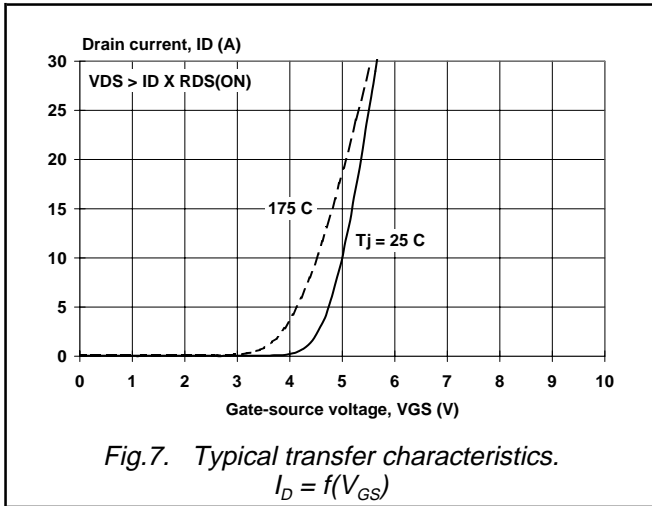
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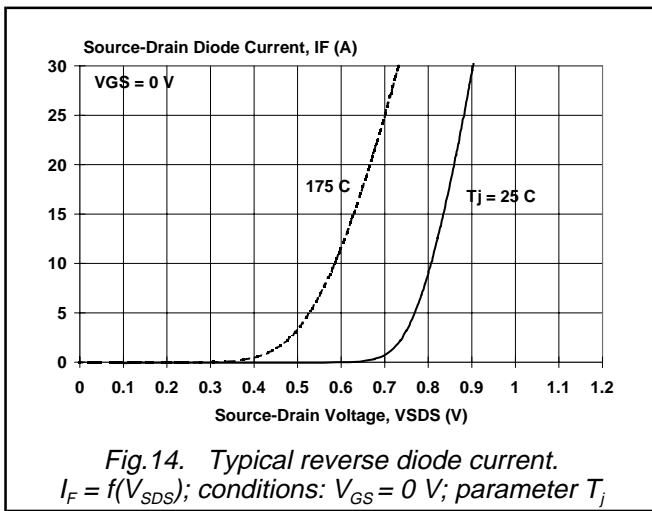
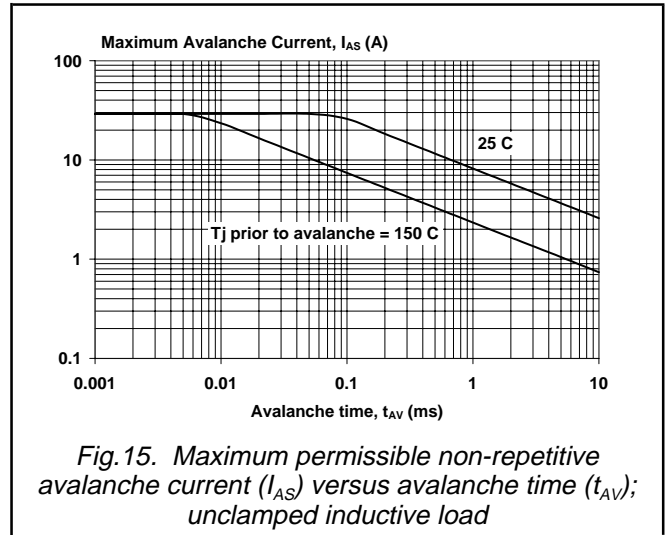
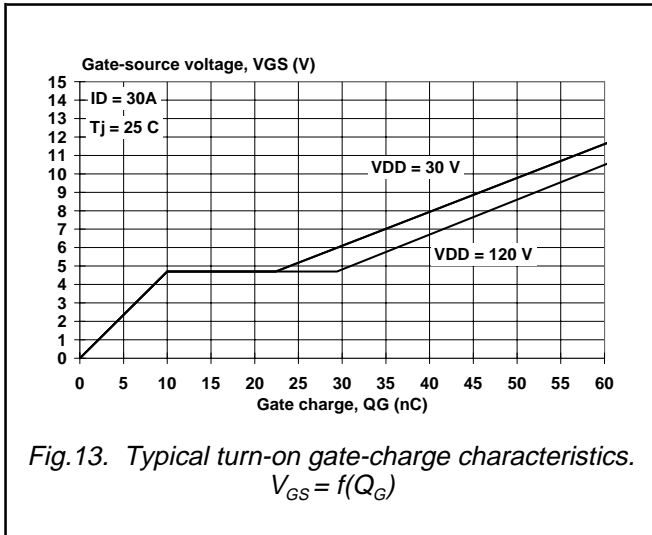
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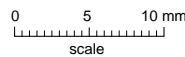
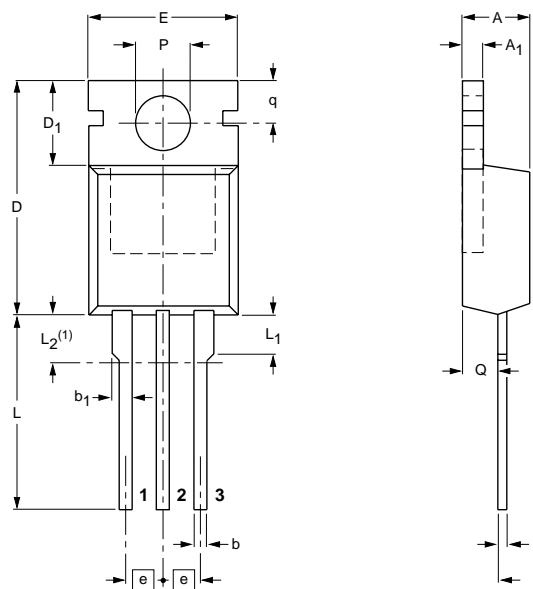


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MECHANICAL DATA

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220 SOT78



DIMENSIONS (mm are the original dimensions)

| UNIT | A | A ₁ | b | b ₁ | c | D | D ₁ | E | e | L | L ₁ | L ₂ ⁽¹⁾ max. | P | q | Q |
|------|------------|----------------|------------|----------------|------------|--------------|----------------|-------------|------|--------------|----------------|---------------------------------------|------------|------------|------------|
| mm | 4.5 4.1 | 1.39 1.27 | 0.9 0.7 | 1.3 1.0 | 0.7 0.4 | 15.8 15.2 | 6.4 5.9 | 10.3 9.7 | 2.54 | 15.0 13.5 | 3.30 2.79 | 3.0 | 3.8 3.6 | 3.0 2.7 | 2.6 2.2 |

Note

1. Terminals in this zone are not tinned.

| OUTLINE VERSION | REFERENCES | | | EUROPEAN PROJECTION | ISSUE DATE |
|-----------------|------------|--------|------|---------------------|------------|
| | IEC | JEDEC | EIAJ | | |
| SOT78 | | TO-220 | | | 97-06-11 |

Fig. 16. SOT78 (TO220AB); pin 2 connected to mounting base (Net mass:2g)

Notes

1. This product is supplied in anti-static packaging. The gate-source input must be protected against static discharge during transport or handling.
2. Refer to mounting instructions for SOT78 (TO220AB) package.
3. Epoxy meets UL94 V0 at 1/8".

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PHP30NQ15T, PHB30NQ15T

MECHANICAL DATA

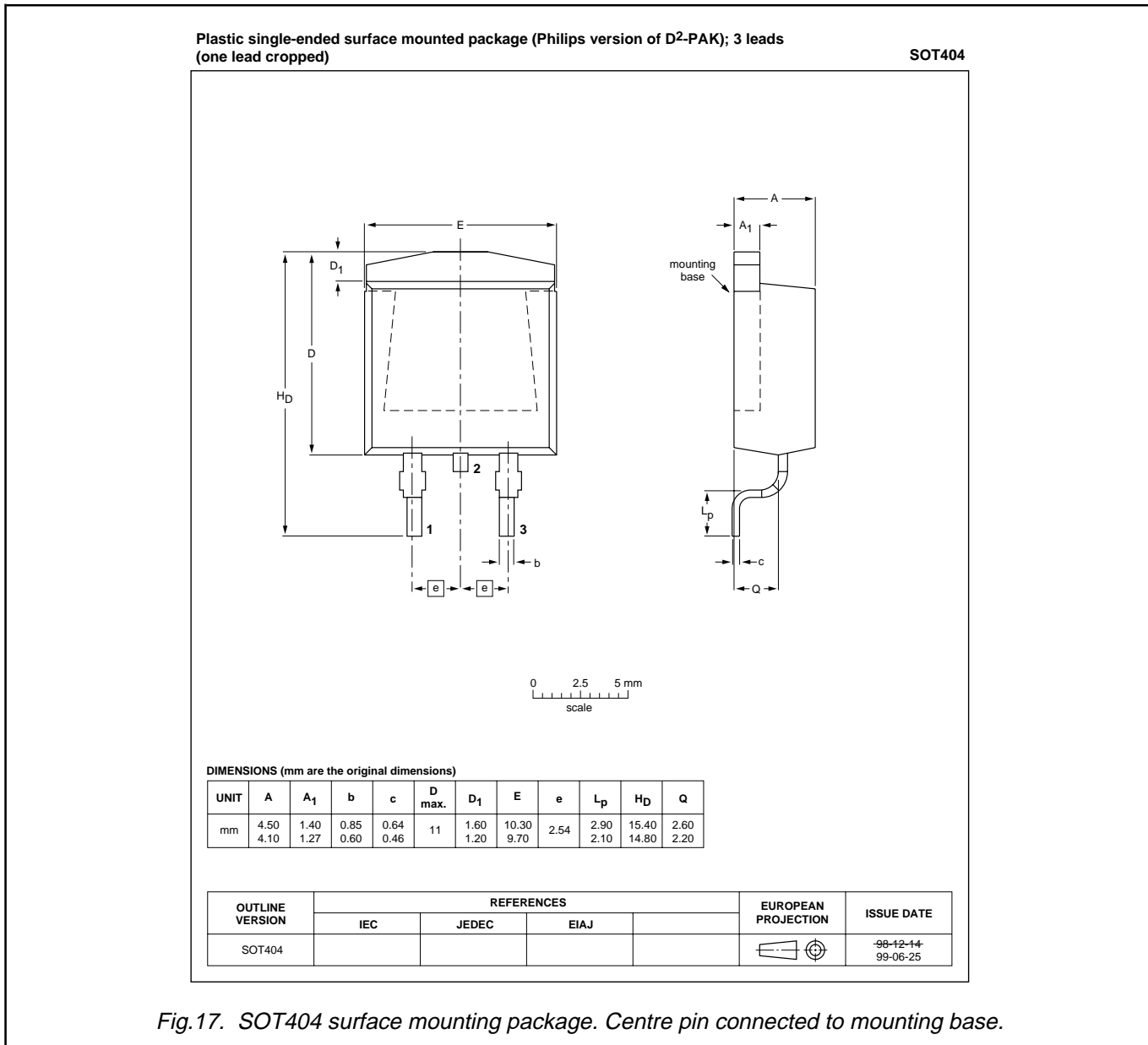


Fig.17. SOT404 surface mounting package. Centre pin connected to mounting base.

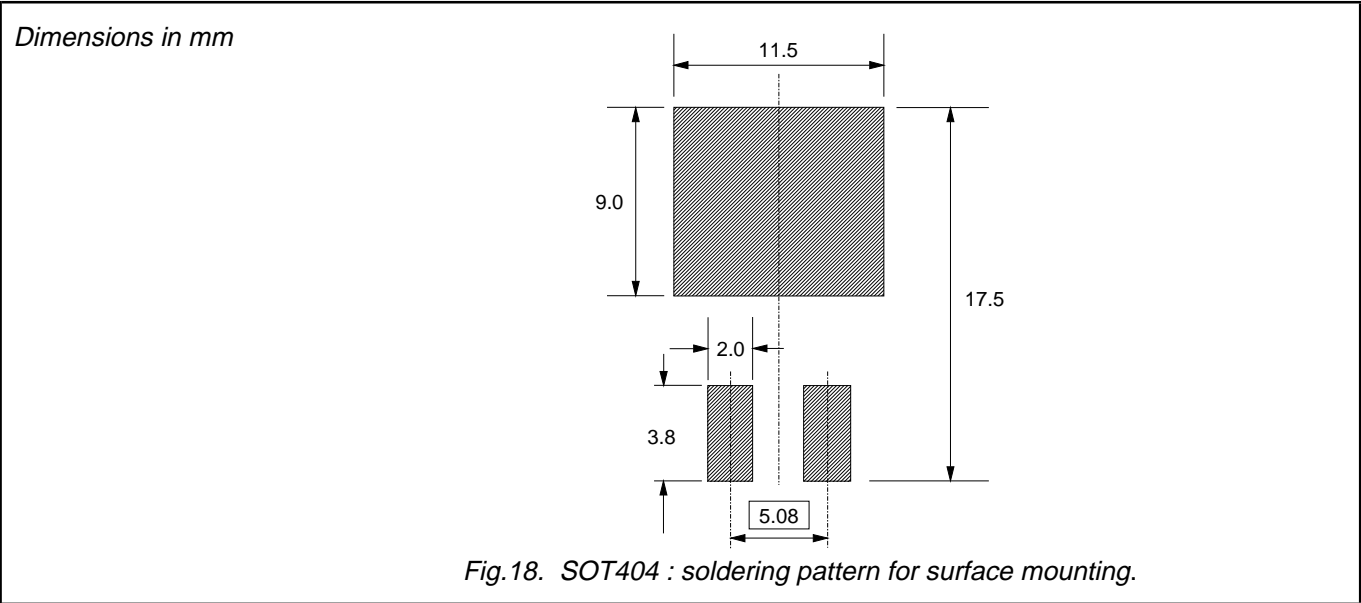
Notes

1. This product is supplied in anti-static packaging. The gate-source input must be protected against static discharge during transport or handling.
2. Refer to SMD Footprint Design and Soldering Guidelines, Data Handbook SC18.
3. Epoxy meets UL94 V0 at 1/8".

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MOUNTING INSTRUCTIONS



DEFINITIONS

| | |
|--|---|
| Data sheet status | |
| Objective specification | This data sheet contains target or goal specifications for product development. |
| Preliminary specification | This data sheet contains preliminary data; supplementary data may be published later. |
| Product specification | This data sheet contains final product specifications. |
| Limiting values | |
| Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability. | |
| Application information | |
| Where application information is given, it is advisory and does not form part of the specification. | |
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